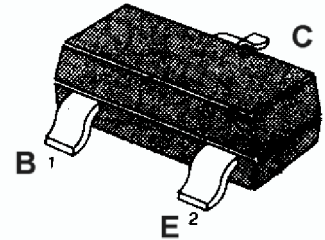


APPLICATION: High Frequency Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	35	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _c	20	mA
Collector Power Dissipation	P _c	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2.Emitter 3.Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	40		200		V _{CE} = 6V, I _c = 1mA
Collector Cut-off Current	I _{CB0}			0.1	μA	V _{CB} = 25V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 3V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	35			V	I _c =0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	30			V	I _c = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	4			V	I _E = 0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.2	V	I _c = 10mA, I _B = 1mA
Gain bandwidth product	f _T	400	600		MHz	I _c = 1mA, V _{CE} = 6V
Common Base Output Capacitance	C _{ob}			2	PF	V _{CB} = 10V, I _E =0, f = 1MHz
Noise Figure	N _F		1	3	dB	V _{CE} =6V, I _c =1mA, f=100MHz, R _g =10KΩ

h_{FE} Classification And Marking

Print Mark

C23

Classification

 h_{FE}

40~200